

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	215493	(nitrogen or N2 or N?sub?2 or nitrogen-rich) with (treat\$4 or expos\$4 or creat\$4 or form\$4)	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD_B	2003/06/27 12:36
2	BRS	L2	7207	1 and (adhes\$4 or adhen\$4) and semiconductor	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD_B	2003/06/27 12:31
3	BRS	L3	11022	1 same (insulat\$4 or dielectric or ILD or IMD or low-k or (low adj2 (dielectric or constant or k)) or FSG or (fluorinated adj (glass or silicateglass)) or organosilicate)	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD_B	2003/06/27 12:34
4	BRS	L4	1507	2 and 3	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD_B	2003/06/27 12:34
5	BRS	L5	1244	4 and (opening or via or viahole or trench or groove)	USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD_B	2003/06/27 12:35